

## NTE2321 Silicon NPN Transistor Quad, General Purpose

### Absolute Maximum Ratings:

Collector–Emitter Voltage, $V_{CEO}$ .....	30V
Collector–Base Voltage, $V_{CBO}$ .....	60V
Emitter–Base Voltage, $V_{EBO}$ .....	5V
Continuous Collector Current, $I_C$ .....	500mA
Total Device Dissipation ( $T_A = +25^\circ\text{C}$ , Each Transistor), $P_D$ .....	0.65W
Derate Above $25^\circ\text{C}$ .....	5.2mW/ $^\circ\text{C}$
Total Device Dissipation ( $T_A = +25^\circ\text{C}$ , Total Device), $P_D$ .....	1.9W
Derate Above $25^\circ\text{C}$ .....	15.2mW/ $^\circ\text{C}$
Operating Junction Temperature Range, $T_J$ .....	$-65^\circ$ to $+200^\circ\text{C}$
Storage Temperature Range, $T_{stg}$ .....	$-65^\circ$ to $+200^\circ\text{C}$

### Electrical Characteristics: ( $T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>OFF Characteristics</b>						
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10\text{mA}$ , $I_B = 0$ , Note 1	40	–	–	V
Collector–Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu\text{A}$ , $I_E = 0$	60	–	–	V
Emitter–Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}$ , $I_C = 0$	5	–	–	V
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 50\text{V}$ , $I_E = 0$	–	–	50	nA
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 3\text{V}$ , $I_E = 0$	–	–	50	nA
<b>ON Characteristics</b>						
DC Current Gain	$h_{FE}$	$V_{CE} = 10\text{V}$ , $I_C = 10\text{mA}$	75	–	–	
		$V_{CE} = 10\text{V}$ , $I_C = 150\text{mA}$	100	–	–	
		$V_{CE} = 10\text{V}$ , $I_C = 300\text{mA}$	30	–	–	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 150\text{mA}$ , $I_B = 15\text{mA}$	–	–	0.4	V
		$I_C = 300\text{mA}$ , $I_B = 30\text{mA}$	–	–	1.6	V
<b>Small–Signal Characteristics</b>						
Current Gain–Bandwidth Product	$f_T$	$V_{CE} = 20\text{V}$ , $I_C = 20\text{mA}$ , $f = 100\text{MHz}$ , Note 1	200	350	–	MHz
Output Capacitance	$C_{obo}$	$V_{BE} = 19\text{V}$ , $I_E = 0$ , $f = 1\text{MHz}$	–	4.5	8.0	pF
Input Capacitance	$C_{ibo}$	$V_{BE} = 0.5\text{V}$ , $I_C = 0$ , $f = 1\text{MHz}$	–	17	30	pF

Note 1. Pulse test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

**Electrical Characteristics (Cont'd):** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Switching Characteristics</b>						
Turn-On Time	$t_{on}$	$V_{CC} = 30\text{V}, V_{BE(off)} = 0.5\text{V}, I_C = 150\text{mA}, I_{B1} = 15\text{mA}$	–	25	–	ns
Turn-Off Time	$t_{off}$	$V_{CC} = 30\text{V}, I_C = 150\text{mA}, I_{B1} = I_{B2} = 15\text{mA}$	–	250	–	ns

**Pin Connection Diagram**

